

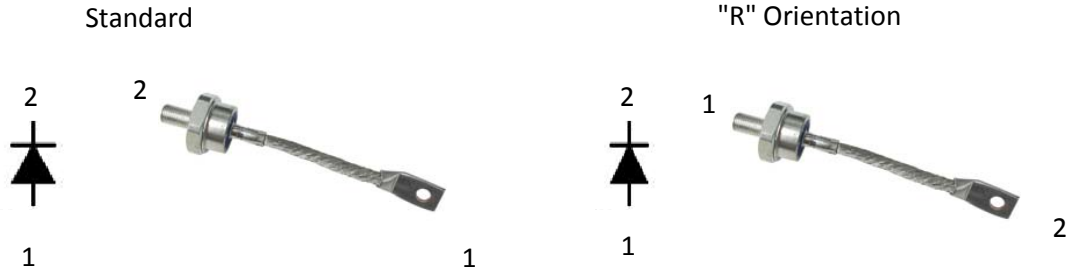
## Silicon Standard Recovery Diode

$V_{RRM} = 200\text{ V} - 1400\text{ V}$   
 $I_F = 100\text{ A}$

### Features

- High Surge Capability
- Types up to 1400 V  $V_{RRM}$

DO-8 Package



Maximum ratings, at  $T_j = 25\text{ °C}$ , unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	1N3295A(R)	1N3296A(R)	1N3297A(R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		1000	1200	1400	V
DC blocking voltage	$V_{DC}$		1000	1200	1400	V
Continuous forward current	$I_F$	$T_C \leq 130\text{ °C}$	100	100	100	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$ , $t_p = 8.3\text{ ms}$	2300	2300	2300	A
$I_2t$ for fusing	$I_2t$	60 Hz Half wave	22000	22000	22000	A <sup>2</sup> sec
Operating temperature	$T_j$		-40 to 200	-40 to 200	-40 to 200	°C
Storage temperature	$T_{stg}$		-40 to 200	-40 to 200	-40 to 200	°C

Electrical characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	1N3295A(R)	1N3296A(R)	1N3297A(R)	Unit
Diode forward voltage	$V_F$	$I_F = 100\text{ A}$ , $T_j = 130\text{ °C}$	1.5	1.5	1.5	V
Reverse current	$I_R$	$V_R = V_{RRM}$ , $T_j = 130\text{ °C}$	11	9	7	mA

### Thermal characteristics

Thermal resistance, junction - case	$R_{thJC}$		0.40	0.40	0.40	°C/W
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**Electrical Characteristics**

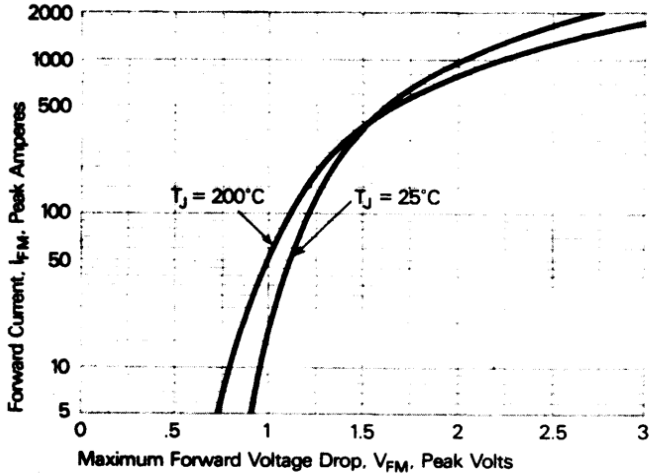


Figure 1. Forward Current vs. Forward Voltage.

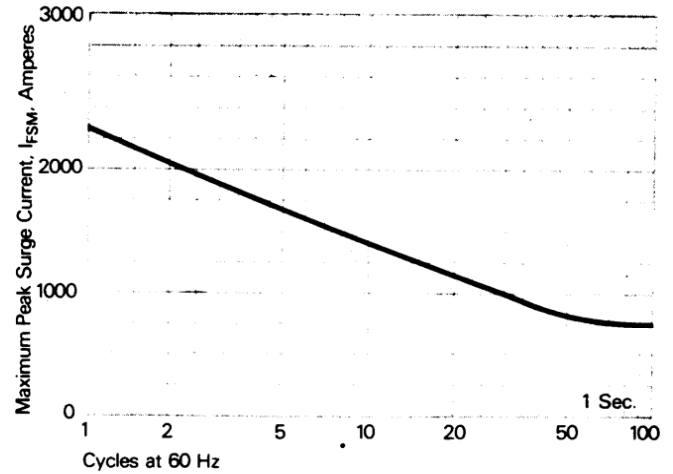


Figure 2. Maximum allowable surge current at rated load conditions.

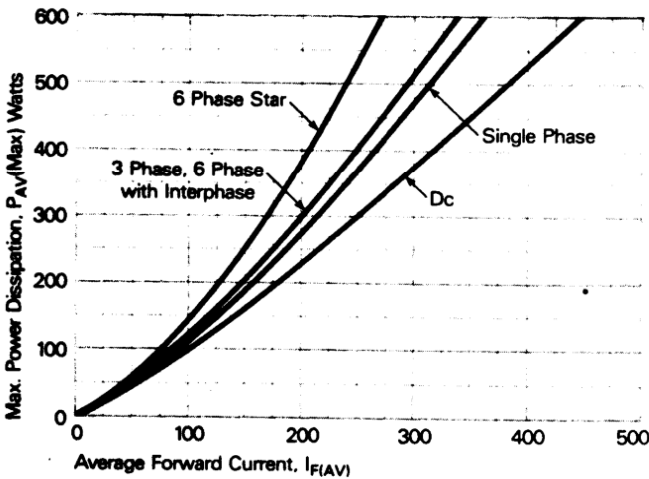


Figure 3. Power dissipation vs. Average forward current.

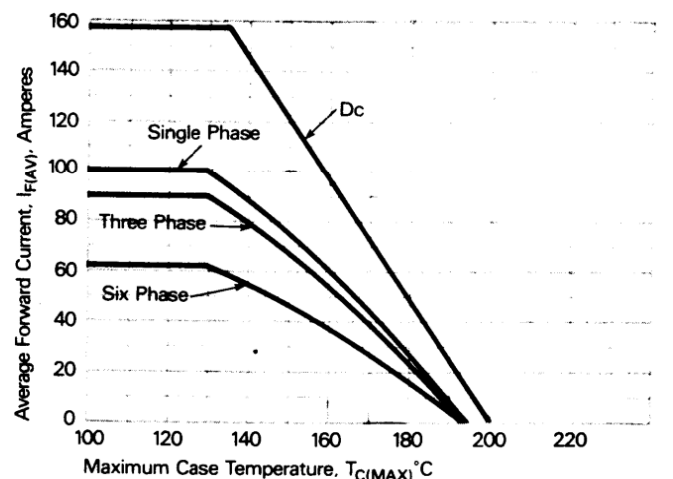


Figure 4. Forward Current vs. Case Temperature.

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